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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

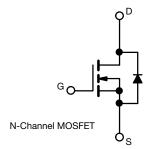


PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.013				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.012				
I _D (A)	75				
Configuration	Single				
Package	PowerPAK SO-8L				

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-source voltage		V_{DS}	60	V		
Gate-source voltage		V_{GS}	± 20	V		
Continuous drain current	T _C = 25 °C	1	75			
	T _C = 125 °C	I _D	43			
Continuous source current (diode conduction)		I _S	75	Α		
Pulsed drain current ^a		I _{DM}	130			
Single pulse avalanche current	L = 0.1 mH	I _{AS}	31			
Single pulse avalanche energy	L=0.11IIII	E _{AS}	48	mJ		
Maximum power dissipation	T _C = 25 °C	Р	187	W		
	T _C = 125 °C	P _D	62	VV		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C		
Soldering recommendations (peak temperature		260	C			

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount b	R_{thJA}	42	°C/W		
Junction-to-case (drain)		R_{thJC}	0.8	C/VV		

Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static					•		
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		60	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		2.0	2.5	V
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	250	
On-state drain current a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	30	-	-	Α
		V _{GS} = 10 V	I _D = 15 A	-	0.009	0.012	
Duein account on state accietance 2		V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.025	Ω
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.033	
		V _{GS} = 4.5 V		-	0.010	0.013	
Forward transconductance b	9 _{fs}	V_{DS}	= 15 V, I _D = 10 A	-	79	-	S
Dynamic ^b							•
Input capacitance	C _{iss}			-	2215	3100	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	202	283	pF
Reverse transfer capacitance	C _{rss}			-	69	97	
Total gate charge ^c	Qg			-	38	57	
Gate-source charge c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 15 \text{ A}$	-	8	-	nC
Gate-drain charge ^c	Q _{gd}			-	6	-	
Gate resistance	R _g	f = 1 MHz		0.9	1.8	2.7	Ω
Turn-on delay time c	t _{d(on)}			-	11	17	
Rise time ^c	t _r	V _{DD} =	$V_{DD} = 30 \text{ V}, R_{L} = 2.0 \Omega$		4	6	ns
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 15 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	29	44	
Fall time ^c	t _f			-	3	5	
Source-Drain Diode Ratings and Char-	acteristics ^b						
Pulsed current ^a	I _{SM}			-	-	130	Α
Forward voltage	V_{SD}	I _F = 10 A, V _{GS} = 0 V		-	-	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 10 A, dl/dt = 100 A/μs		-	21	42	ns
Body diode reverse recovery charge	Q _{rr}			-	18	36	nC
Reverse recovery fall time	t _a			-	14	-	ns
Reverse recovery rise time	t _b			-	7	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	1.8	-	Α

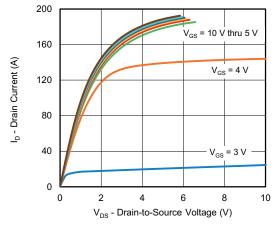
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

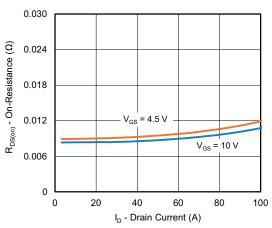
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



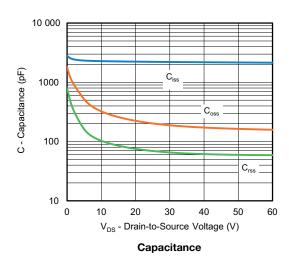
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

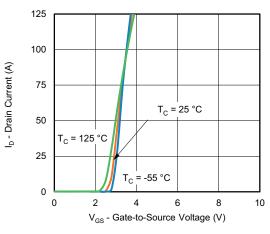


Output Characteristics

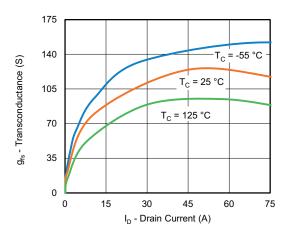


On-Resistance vs. Drain Current

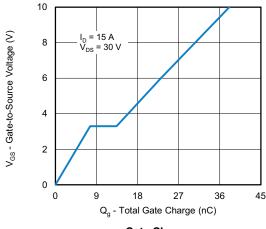




Transfer Characteristics



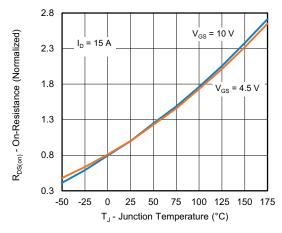
Transconductance



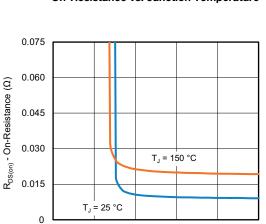
Gate Charge



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



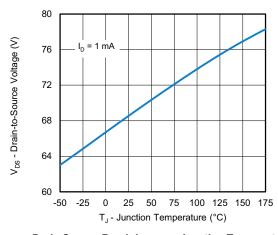
On-Resistance vs. Junction Temperature



 $\label{eq:VGS} \mbox{V}_{\mbox{GS}} \mbox{-} \mbox{Gate-to-Source Voltage (V)}$ On-Resistance vs. Gate-to Source Voltage

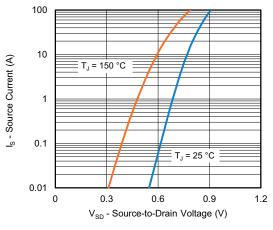
8

10

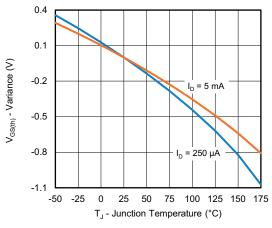


Drain Source Breakdown vs. Junction Temperature Note

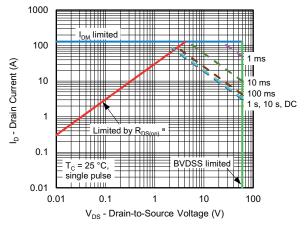
a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



Source Drain Diode Forward Voltage



Threshold Voltage



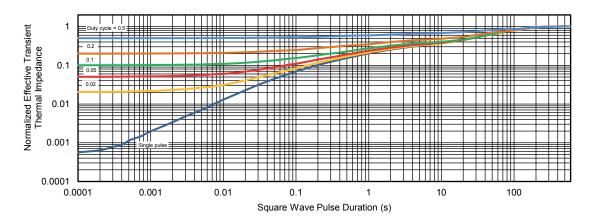
Safe Operating Area

0

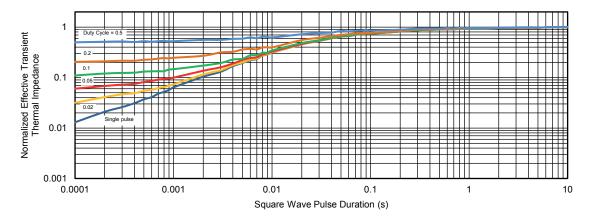
2



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

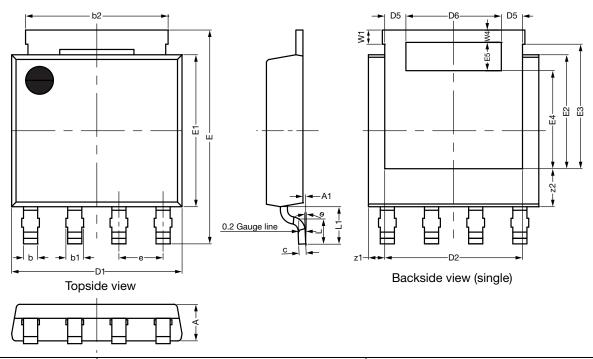
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77465.



PowerPAK® SO-8L (PPKSO8LWLA) Case Outline 3



DIM.	MILLIMETERS			INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	1.00	1.05	1.10	0.039	0.041	0.043
A1	0.00		0.127	0.000		0.005
b	0.33	0.41	0.49	0.013	0.016	0.019
b1	0.43	0.51	0.59	0.017	0.020	0.023
b2	4.00	4.10	4.20	0.157	0.161	0.165
С	0.15	0.20	0.25	0.006	0.008	0.010
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D5	0.51	0.61	0.71	0.020	0.024	0.028
D6	2.64	2.74	2.84	0.104	0.108	0.112
е		1.27 BSC 0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	3.18	3.28	3.38	0.125	0.129	0.133
E3	3.48	3.58	3.68	0.137	0.141	0.145
E4	2.72	2.82	2.92	0.107	0.111	0.115
E5	0.71	0.81	0.91	0.028	0.032	0.036
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
W1	0.31	0.41	0.51	0.012	0.016	0.020
W4	0.31	0.36	0.41	0.012	0.014	0.016
z1	0.37	0.47	0.57	0.015	0.019	0.022
z2	0.99	1.09	1.19	0.039	0.043	0.047
θ	0°		5°	0°		5°

ECN: C22-1223-Rev. C, 19-Dec-2022

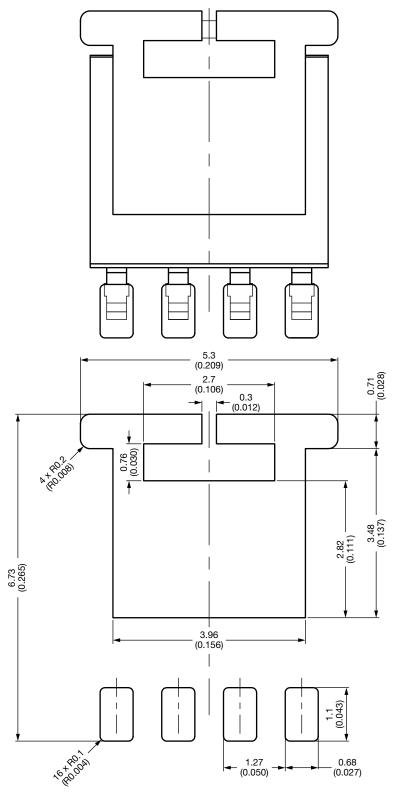
DWG: 6067 **Note**

Millimeter will govern

Revison: 19-Dec-2022 1 Document Number: 76666



Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)



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